EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	16352	"MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:22
S2	409	"MOCVD" and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:36
S3	0	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S4	299	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S5	7	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:37
S6	7	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:38
S7	2	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow$4 and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:51
S8	130	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:52

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S9	76	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 holder or support)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:53
S10	39	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:53
S11	29	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:54
S12	25	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:56
S13	0	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and gradient	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:54
S14	882909	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 11:56
S15	6	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:07
S16	25	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:08

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S17	39	(epitaxial near4 grow$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:27
S18	56	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:31
S19	56	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:32
S20	51	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:36
S21	17	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:39
S22	9	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and "InGaAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:41
S23	2	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow$4 and "InGaAs" and "InAlAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:47
S24	8	"MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and grow$4 and "InGaAs" and "InAlAs"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/03 12:47

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S25	6233	"MOCVD" near8 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
S26	70	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
S27	0	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:23
S28	25	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:24
S29	16	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:24
S30	5	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:25
S31	5	"MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer)) and grow$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:27

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S32	57541	(epitaxial near4 grow$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:27
S33	2471828	((epitaxial near4 grow$4) near8 semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:28
S34	33536	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:28
S35	1837	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:29
S36	0	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8 "MOCVD")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:29
S37	41	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:30
S38	20	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:37
S39	0	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and arsenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:30

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S40	16	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:33
S41	15	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:35
S42	2	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction and "InP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:36
S43	11	"5494833"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:36
S44	2	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and arsenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:38
S45	9	((epitaxial near4 grow$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and ("InGaAs" or "InAlAs")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:43
S46	19224	(semiconductor or substrate or wafer) near8 "InP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:44

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S47	5061	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:45
S48	823	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:46
S49	1	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and (angle near4 gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:47
S50	134	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:48
S51	97	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:48
S52	21	(semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate)) and (density near4 (semiconductor or wafer or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:01
S53	44654	(epitax$4 near growth)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:02

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S54	10823	(epitax$4 near growth) and (substrate or wafer or carrier) near9 (support or holder or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:03
S55	12321	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:03
S56	1942	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:03
S57	1203	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near9 (substrate or wafer or carrier or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:03
S58	1145	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:04
S59	357	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:05

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S60	274	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:05
S61	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and (angle near4 gradient)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:06
S62	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and (angle near9 gradient)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:06
S63	61	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:06
S64	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and gradient	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 08:07

S65	61	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:19
S66	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and (thick$4 near9 ".05")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:20
S67	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and (thickness near9 ".05")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:20
S68	45	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) near9 thick$4 and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:27
S69	1	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) near9 thick$4 and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and morphology	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:28

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S70	0	(epitax$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) near9 thick$4 and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and morph$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 09:28